

MOSFET - Power, Single N-Channel 80 V, 4.5 mΩ, 103 A

NVMFS6H824N

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS6H824NWF – Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halide Free, and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	80	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	I_D	103	A
		73	
Power Dissipation $R_{\theta JC}$ (Note 1)	P_D	115	W
		58	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	I_D	19	A
		13	
Power Dissipation $R_{\theta JA}$ (Notes 1 & 2)	P_D	3.8	W
		1.9	
Pulsed Drain Current	I_{DM}	626	A
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	96	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 7 \text{ A}$)	E_{AS}	736	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

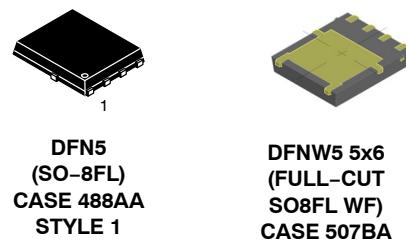
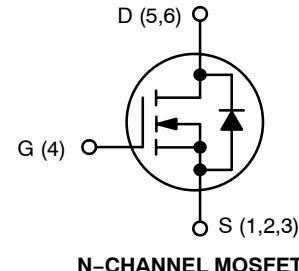
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

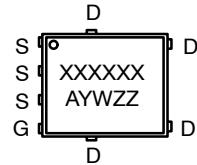
Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	1.3	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39.8	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
80 V	4.5 mΩ @ 10 V	103 A



MARKING DIAGRAM



XXXXXX = 6H824N
(NVMFS6H824N) or
824NWF
(NVMFS6H824NWF)

A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMFS6H824N

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$		80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				43		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 80 \text{ V}$	$T_J = 25^\circ\text{C}$		10		μA
			$T_J = 125^\circ\text{C}$			100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = 20 \text{ V}$				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 140 \mu\text{A}$		2.0		4.0	V
Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				-7.2		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 20 \text{ A}$		3.7	4.5	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 15 \text{ V}, I_D = 20 \text{ A}$			75		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 40 \text{ V}$		2470		pF
Output Capacitance	C_{OSS}			342		
Reverse Transfer Capacitance	C_{RSS}			11		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 40 \text{ V}; I_D = 30 \text{ A}$		38		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$		$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 40 \text{ V}; I_D = 30 \text{ A}$	7.4		
Gate-to-Source Charge	Q_{GS}			12		
Gate-to-Drain Charge	Q_{GD}			7.0		
Plateau Voltage	V_{GP}			4.7		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 64 \text{ V}, I_D = 30 \text{ A}, R_G = 2.5 \Omega$		20		ns
Rise Time	t_r			52		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			55		
Fall Time	t_f			42		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_S = 20 \text{ A}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 125^\circ\text{C}$		0.7		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 30 \text{ A}$			52		ns
Charge Time	t_a				32		
Discharge Time	t_b				19		
Reverse Recovery Charge	Q_{RR}				67		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

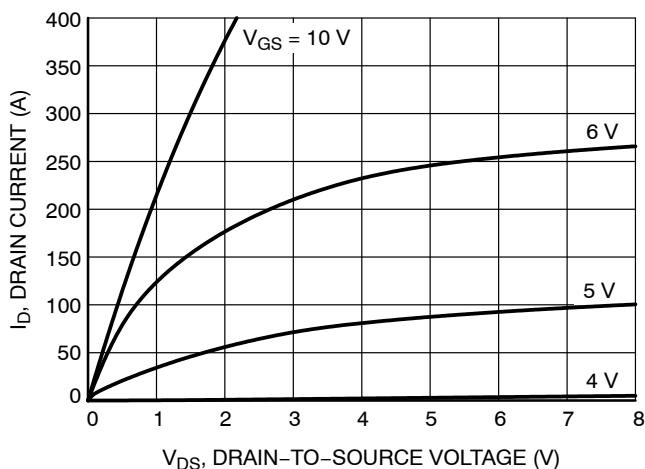


Figure 1. On-Region Characteristics

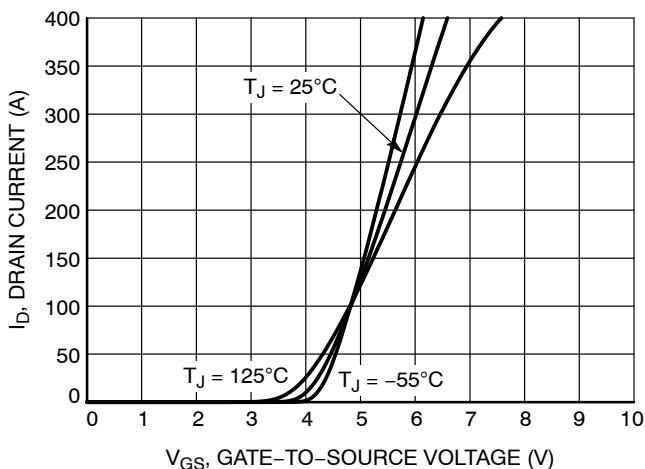


Figure 2. Transfer Characteristics

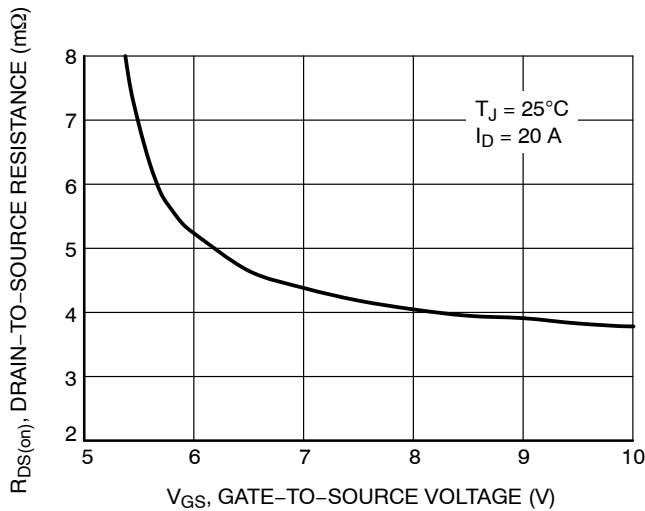


Figure 3. On-Resistance vs. Gate-to-Source Voltage

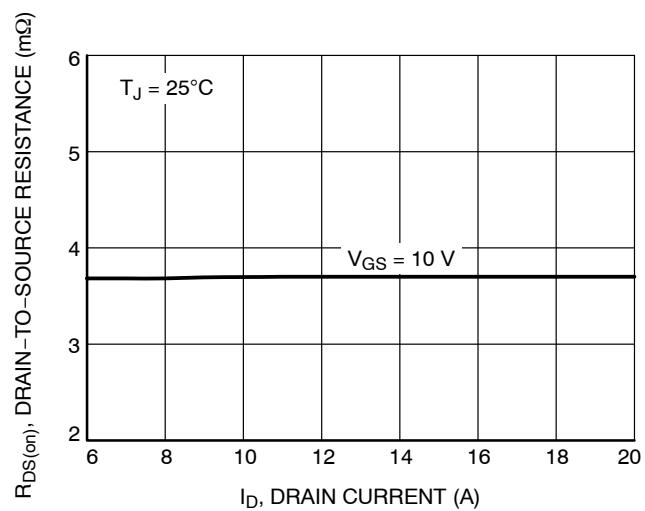


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

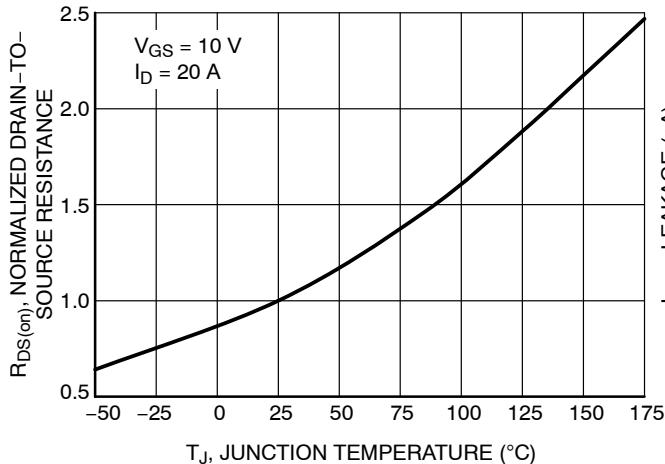


Figure 5. On-Resistance Variation with Temperature

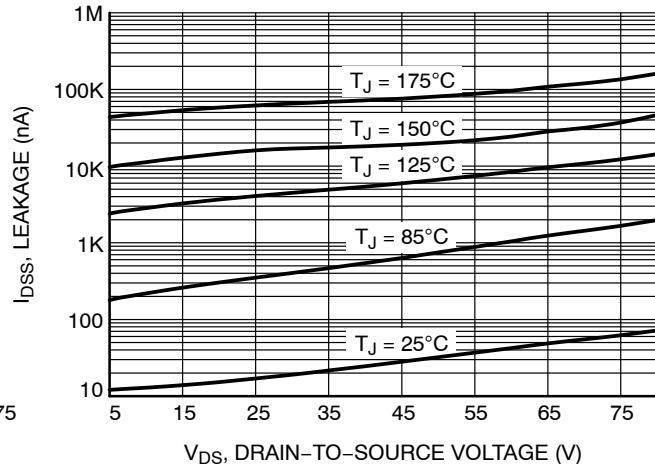
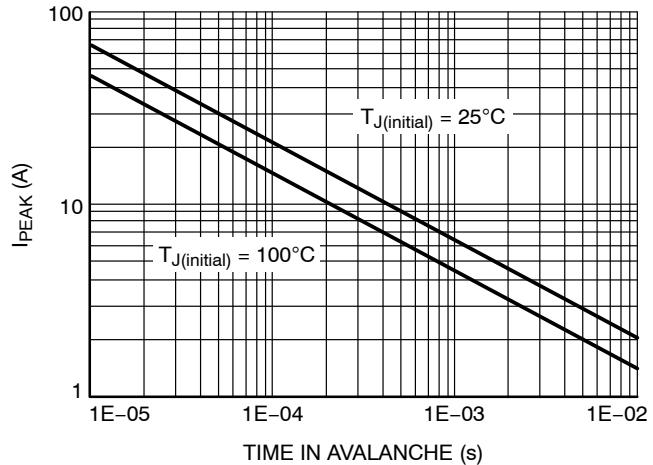
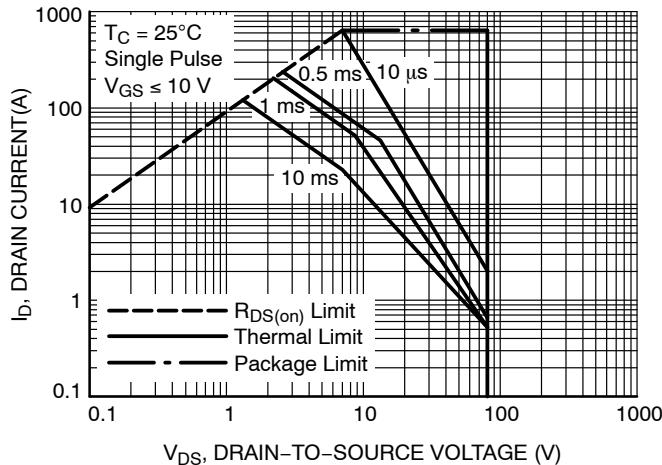
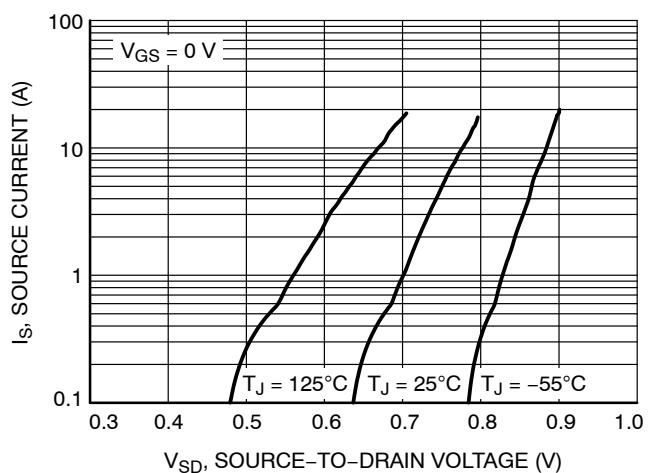
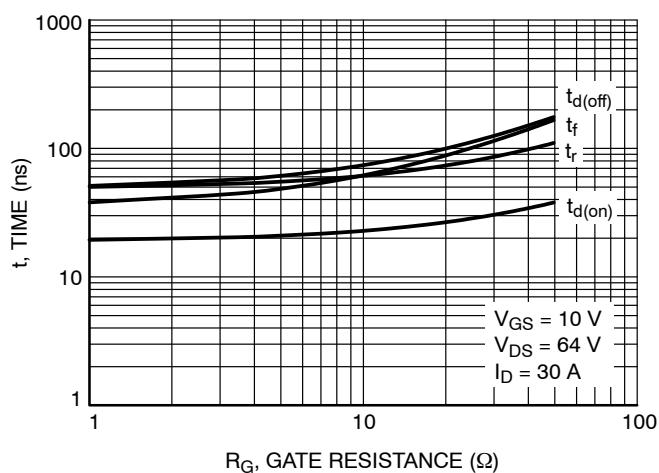
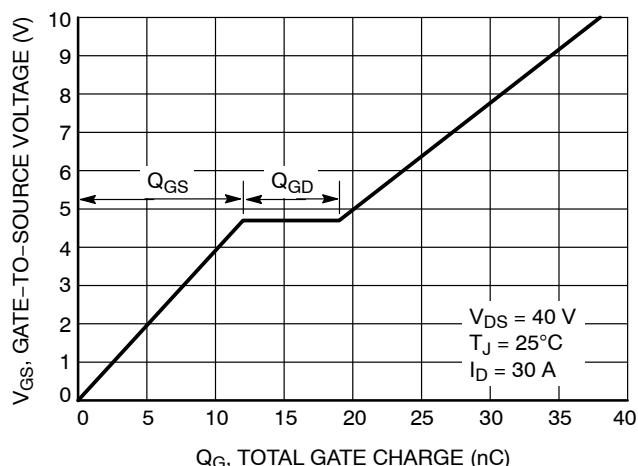
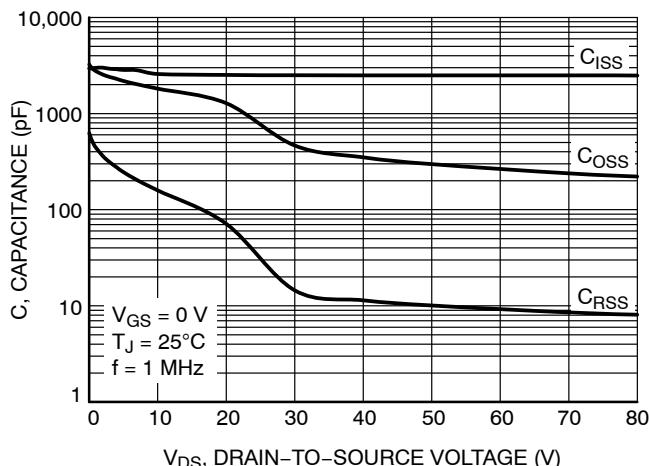


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)



TYPICAL CHARACTERISTICS (continued)

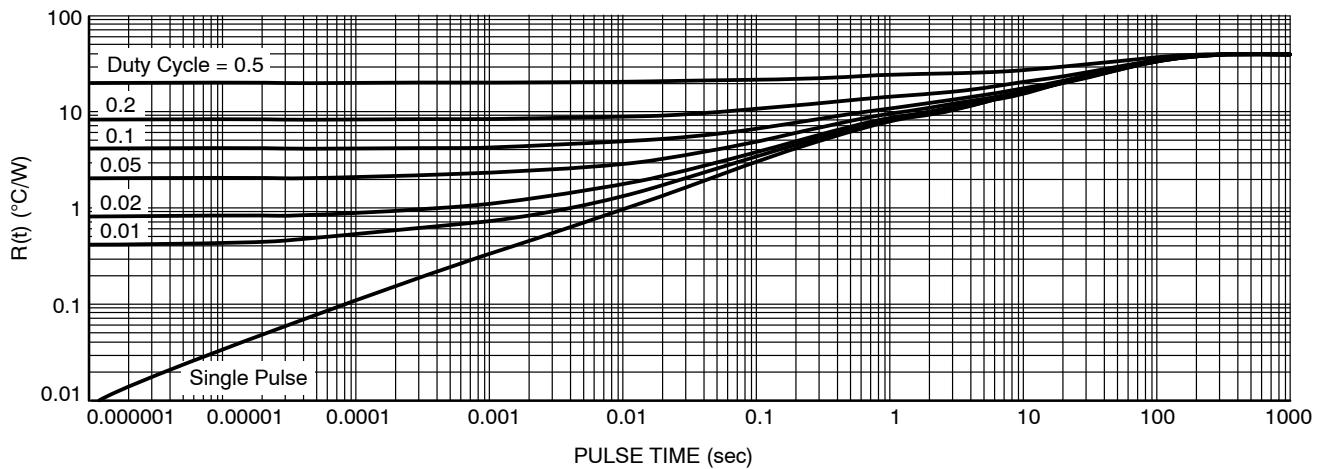
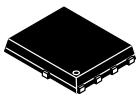


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFS6H824NT1G	6H824N	DFN5 (Pb-Free, Halide Free)	1500 / Tape & Reel
NVMFS6H824NWFT1G	824NWF	DFNW5 (Pb-Free, Halide Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).



SCALE 2:1

**DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N**

DATE 25 JUN 2018

NOTES:

NOTE:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
n	0 °		12 °

GENERIC MARKING DIAGRAM*



xxxxxx = Specific Device Code

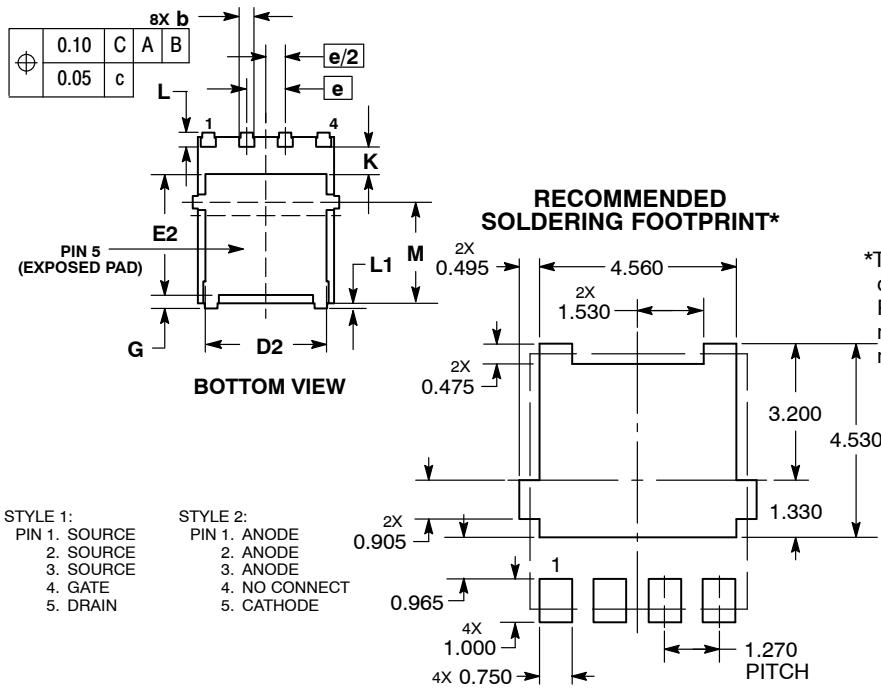
A = Assembly Location

Y = Year

W = Work Week

ZZ = Lot Traceability

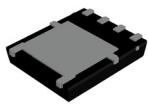
*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "■",
may or may not be present. Some products
may not follow the Generic Marking.



*For additional information on our Pb-Free strategy and soldering details, please download the [onsemi](#) Soldering and Mounting Techniques Reference Manual, SOI DERRM/D.

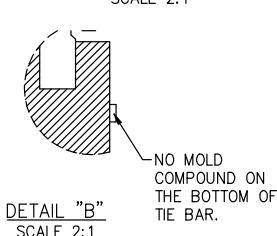
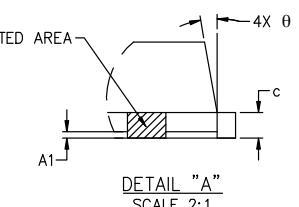
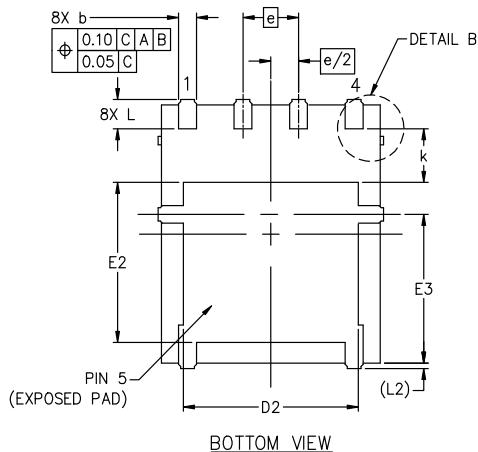
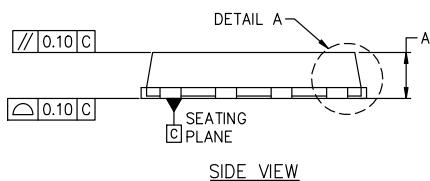
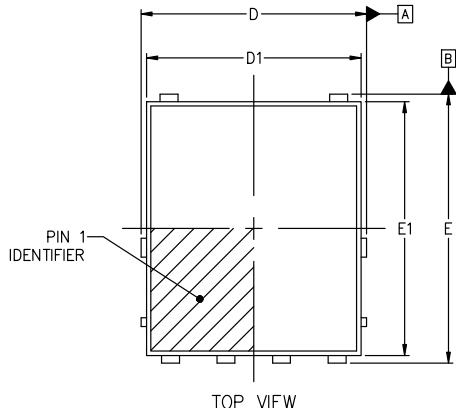
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DFNW5 4.90x5.90x1.00, 1.27P
CASE 507BA
ISSUE C

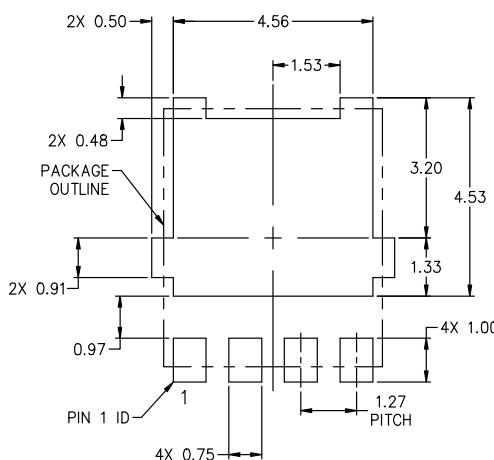
DATE 19 SEP 2024



NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

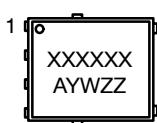
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D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
E3	3.00	3.40	3.80
e		1.27 BSC	
k	1.20	1.35	1.50
L	0.51	0.57	0.71
L2		0.15 REF.	
θ	0°	6°	12°



RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***



XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking.
 Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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